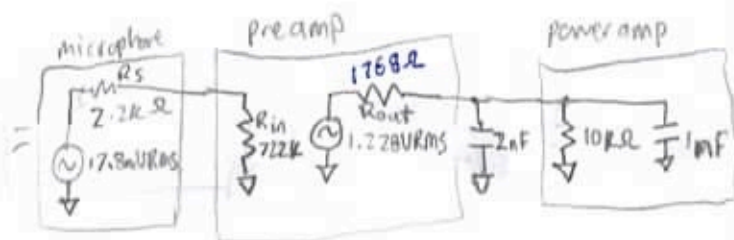
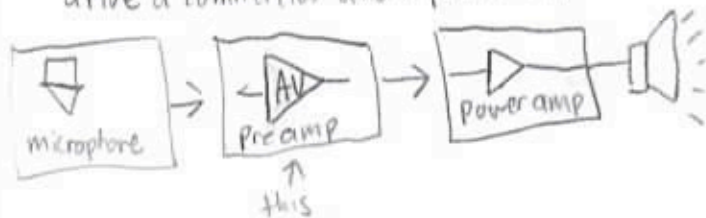


Step 1: determine required

- gain
- input & output impedances
- frequency response
- output signal swing
- sometimes  $\uparrow$  must be deduced

ex: design a small-signal preamplifier  
for a Panasonic WM-61A

electret condenser microphone to  
drive a commercial audio power amplifier



microphone specs:

"nominal" signal level: 17.8 mVRMS @ 94 dB SPL

output impedance: 2.2 k $\Omega$

$\therefore R_{in}$  should be "much higher" than 2.2 k $\Omega$   
to avoid voltage dividing an already small  
signal

• Perhaps try for  $R_{in} > 22 \text{ k}\Omega$

Frequency range: 50 Hz to 15 kHz

$\hookrightarrow$  amplifier response should exceed this on both sides

$\hookrightarrow -3 \text{ dB @ } 30 \text{ kHz} \sim -1 \text{ dB @ } 15 \text{ kHz}$

so perhaps shoot for 25 Hz to 30 kHz

$\uparrow$   $\uparrow$   
 $f_L$   $f_H$

Power-amp specs:

nominal input sensitivity: 1.228 VRMS

input impedance:  $R_{in} = 10 \text{ k}\Omega$  in parallel w/ 1 nF

$\hookrightarrow$  let's add a worst-case cable capacitance of 2 nF (fool proof it)

$\therefore C_L(\text{total}) = 3 \text{ nF}$

## Gain calc

$$A_V = \frac{1.228}{0.0178} = 68.99 = 36.78 \text{ dB}$$

∴ this needs a high gain, tend towards

BJT for high  $g_m$  ← (thing for gain)

→ But FETs have higher input impedance

in order to drive  $3 \text{ nF}$  to at least  $30 \text{ kHz}$ ,  
we need  $R_{out}$  less than

$$f_{H_{out}} = \frac{1}{2\pi R_{out} C_L} \rightarrow R_{out} = \frac{1}{2\pi f_H C_L}$$

$$= \frac{1}{2\pi \cdot 30 \text{ kHz} \cdot 3 \text{ nF}} = \underline{1768 \Omega}$$

← collector or drain resistor in this ballpark?

"Nominal" usually means "normal" or "average"

→ could mean peak values well in excess of this

→ so if our preamp must create nominal  $1.228 \text{ V}_{RMS}$ ,  
but could be asked to provide more, how much more?

∴ let's assume we'd like  $10 \text{ dB}$  of headroom

$$\text{factor of } 10^{10/20} = 10^{1/2} = 3.16$$

→ so max output voltage might be  $1.228 \cdot 3.16 = 3.883 \text{ V}_{RMS}$

$$3.883 \cdot \sqrt{2} \cdot Z = 11 \text{ V}_{pp}$$

in summary: our amplifier needs

•  $A_V \approx 37 \text{ dB}$

•  $R_{in} \geq 22 \text{ k}\Omega$

•  $R_{out} \leq 1768 \Omega$

• output swing  $> 11 \text{ V}_{pp}$  into  $10 \text{ k}\Omega \parallel 3 \text{ nF}$  load

• bandwidth better than  $f_L = 25 \text{ Hz}$ ,  $f_H = 30 \text{ kHz}$

step 2: choose suitable electronic device & amplifier config. for specs.

Page 3

specs  
 BW: 25-30kHz  
 AV ≈ 37dB  
 Rin ≥ 22kΩ  
 Rout ≤ 1768Ω  
 Vout ≥ 11Vp-p

• Rin is fairly high; suggests FETs

↳ however, we also need high gain → BJTs

suggest using a Darlington transistor (high gm of BJT w/ very high equivalent β)

↳ use common-emitter amplifier (have to check if inversion is OK)  
 also have to check how much input capacitance we can tolerate (b/c Rs = 2.2kΩ)

step 3:

$$f_{H(in)} \approx \frac{1}{2\pi R_s C_{in}} \rightarrow C_{in} = \frac{1}{2\pi R_s f_{H(in)}} = \frac{1}{2\pi \cdot 2.2k \cdot 60kHz} = 1.2nF$$

choose an approximate operating point and actual device that achieves signal swing, gain, and Rout

↑  
 doubled to be safe

Common-emitter: Rout ≈ Rc

∴ to achieve Rout ≤ 1768, choose Rc = 1.5kΩ

• for low distortion, RL > 2Rc [minimum]

↳ check 10k > 2 · 1.5k, OK

Common-emitter: Av ≈ -gm(Rc || RL)

$$R_c || R_L = 1.5k || 10k = 1.3k$$

∴ need gm >  $\frac{68.99}{1.3k} = 53.07 \frac{mA}{V}$  ← required gain

↳ consistent w/ BJTs!

Ebers-Moll: gm = 35 Ic

$$\therefore I_c > \frac{gm}{35} = \frac{53}{35} = 1.5mA \leftarrow \text{probably doable}$$

we need > 11Vp-p signal swing

∴ Vcc > 11V; but how much more?

• plan to lose a couple volts across RE

• plan to stay a couple volts away from ground

• plan to stay a couple volts away from Vcc

avoid saturation

avoid cutoff



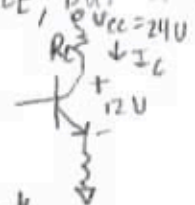
• choose Vcc = 24V (a common voltage regulator value)

• determine approx. VCE max and Pdis

↳ under extreme conditions, VCE → Vcc  
 ∴ VCE max > 24V

↳ we don't know our exact VCE, but it'll likely be ≈ VCE = 12V

$$\therefore \text{approx } I_c \approx \frac{24-12}{1.5k} \rightarrow \frac{12}{1.5k} = 8mA > 1.5mA \text{ ok}$$



$$P_{dis} \approx V_{CE} \cdot I_c = 12 \cdot 8 = 96mW$$

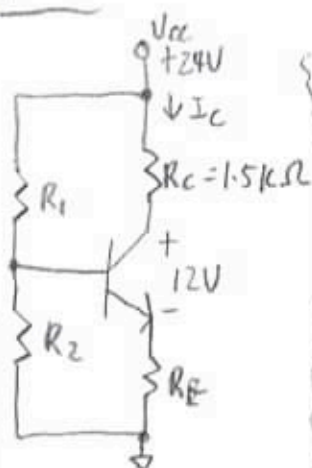
∴ we need to choose a Darlington w/ VCE > 24V  
 Pdis > 96mW

# Step 4: select device and perform load line analysis to determine optimum

Page 4

## Quiescent operating point

chosen device: MPS A14  
NPN darlington,  
Si  
NPN  
 $V_{CE(max)} = 30V$   
 $h_{fe(min)} = 10,000$  (this is  $\beta$ )  
 $P_{max} = 625mW$   
 $C_{ibo} = 5.6pF \approx C_{be}$   
 $C_{obo} = 5.2pF \approx C_{bc}$



→ let's pick 2V across  $R_E$  for DC stability  
(10% of  $V_{CC}$  (loss?) is not uncommon)

$$\therefore R_E \approx \frac{2V}{8mA} = 0.25k\Omega, \text{ pick } R_E = 220\Omega$$

.. Introduce DC load line

.. at DC, net load across transistor is  $R_C + R_E$

.. we can plot this against MPSA14 curves to show possible operating points!

$$I_{C(max)} = \frac{V_{CC}}{R_C + R_E} = \frac{24}{1.72k} = 13.95mA$$

## Continue

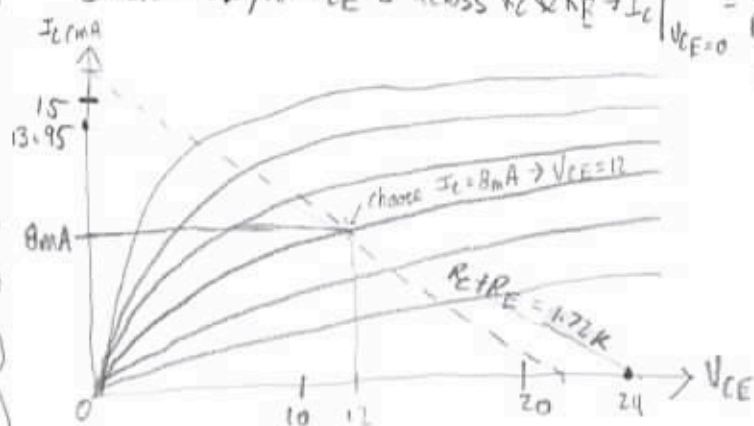
.. steeper AC loadline reduces signal swing

→ that's why you want  $R_L \gg R_C$

→ final available signal swing is  
 $\approx 20.64 - 2 > 18V_{p-p}$  (still ok)

@ Zero  $I_C \rightarrow$  no drop across  $R_C$  &  $R_E \rightarrow V_{CE}|_{I_C=0} = V_{CC}$

@ Zero  $V_{CE}$ , all  $V_{CE}$  is across  $R_C$  &  $R_E \rightarrow I_C|_{V_{CE}=0} = \frac{V_{CC}}{R_C + R_E} = \frac{24}{1.72k} = 13.95mA$



For AC signals need to factor in  $R_L$

→ AC load line superimposed on D.C. one  
actual  $V_{CE} = V_{CC} - I_C(R_C + R_E) = 24 - 8(1.5 + 2.2) = 10.24V$

AC collector load  $= R_C || R_L = 1.5k || 10k = 1.3k$

→ we can draw AC load line with this steeper slope  
→ start w/ quiescent point at  $I_C = 8mA$

$$V_{CE}|_{I_C=8mA} = 10.24 + 8(1.3k) = 20.64V$$

$$I_C|_{\Delta V_{CE} = -10.24V} = 8 + \frac{10.24}{1.3k} = 15.87mA$$

See continue to the left



Step 5  
use quiescent point determined in step 4  
to design D.C. bias network for amplifier

• Darlington

$$\therefore I_c \approx I_E$$

(Very low base current)

$$\therefore V_E = R_E \cdot I_E = 0.220k \cdot 8m = 1.76V$$

$$\text{Darlington: } V_{BE} \approx 1.4V \quad V_B = V_E + 1.4 = 1.76 + 1.4 = 3.16V$$

Pick  $R_2 = 47k\Omega$

$$V_B = V_{CC} \left[ \frac{R_2}{R_1 + R_2} \right]$$

$$3.16 = 24 \left[ \frac{47}{47 + R_1} \right] \rightarrow R_1 = 311k \text{ use } 300k = R_1$$

Check  $R_{in}$

$$R_{in} \approx R_1 \parallel R_2$$

$$= 47k \parallel 300k$$

$$= 40.63k > 22k\Omega \text{ (ok)}$$

Step 6 Mid Frequency SS analysis

$$C_E: A_{v_2} = -g_m (R_C \parallel R_L)$$

$$g_m = 35 I_c = 35 \cdot 8 = 280 \text{ mA/V}$$

$$A_{v_2} \approx -280(1.3k) = -364 \text{ or } 51dB \gg 37dB \text{ (too much gain)}$$

• check input capacitance (Miller time)

$$C_{Bc(in)} = C_{Bc}(1 - A_v) = 5.2(1 - 364) = 1896 \text{ pF} > 1206 \text{ pF} \text{ (not good, too high)}$$

• the solution? Negative feedback

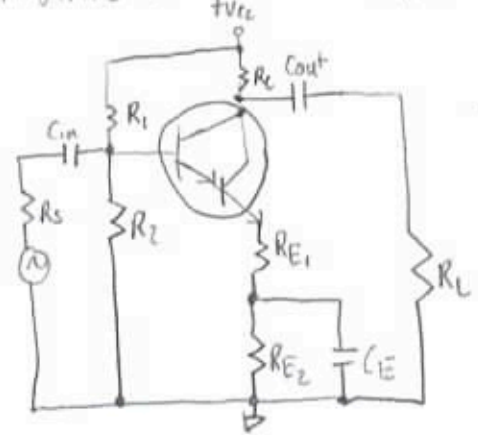
1) external shunt/shunt loop

2) unbypassed emitter resistor

1) works better, but harder to implement

$\therefore$  choose 2)

Negative feedback stuff from step 6



• Set  $R_{E1} + R_{E2}$  to  $220k$   
for D.C. characteristics

• Set  $R_{E1}$  for desired  
feedback factor (for A.C.)

want  $A_v = 68.99$  ignoring polarity inversion  
have  $A_{v0} = 364$

$$A_v = \frac{A_{v0}}{1 + \beta A_{v0}} \rightarrow A_v + \beta A_{v0} A_v = A_{v0} \rightarrow \beta = \frac{A_{v0} - A_v}{A_{v0} \cdot A_v}$$

$$\beta = \frac{364 - 69}{364 \cdot 69} = 0.01175$$

• for local-emitter feedback

$$\beta = \frac{R_E}{R_C \parallel R_L} = \frac{R_{E1}}{1.3k} = 0.01175 \rightarrow R_{E1} = 0.01175 \cdot 1.3k = 0.01528k\Omega \text{ use } R_{E1} = 15\Omega$$

high- $A_{v0}$  approximation:

$$A_v \approx \frac{R_C \parallel R_L}{R_E} \rightarrow R_{E1} = \frac{1.3k}{69} = 18.84\Omega \text{ (might have made } A_v \text{ too low because } 364 \gg 69)$$

• what's left?

• recheck HF response

• design LF components to achieve  $f_L < 25Hz$

make most expensive cap  
dominant pole  $\rightarrow C_E$